Silicon NPN Power Transistors 2N3226

DESCRIPTION

·With TO-3 package
·Excellent safe operating area
·Low collector saturation voltage

APPLICATIONS

·For power amplifier and switching circuits applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

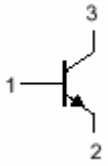

Fig.1 simplified outline (TO-3) and symbol

ABSOLUTE MAXIMUM RATINGS (Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	35	V
V_{CEO}	Collector-emitter voltage	Open base	35	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		5	A
P_D	Total power dissipation	T_C=25□	75	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-65~200	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{(th)\,jc}$	Thermal resistance junction to case	1.17	□/W

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=0.2A ;I_B=0	35			V
$V_{CE(sat)-1}$	Collector-emitter saturation voltage	I_C=3A; I_B=0.3A			1.0	V
$V_{CE(sat)-2}$	Collector-emitter saturation voltage	I_C=5A ;I_B=1.0A			2.0	V
$V_{BE(on)}$	Base-emitter on voltage	I_C=3A ; V_{CE}=4V			2.0	V
I_{CEO}	Collector cut-off current	V_{CE}=35V; I_B=0			1.0	mA
I_{CBO}	Collector cut-off current	V_{CB}=35V; I_E=0			0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			0.1	mA
h_{FE-1}	DC current gain	I_C=1A ; V_{CE}=4V	40			
h_{FE-2}	DC current gain	I_C=3A ; V_{CE}=4V	20			

PACKAGE OUTLINE

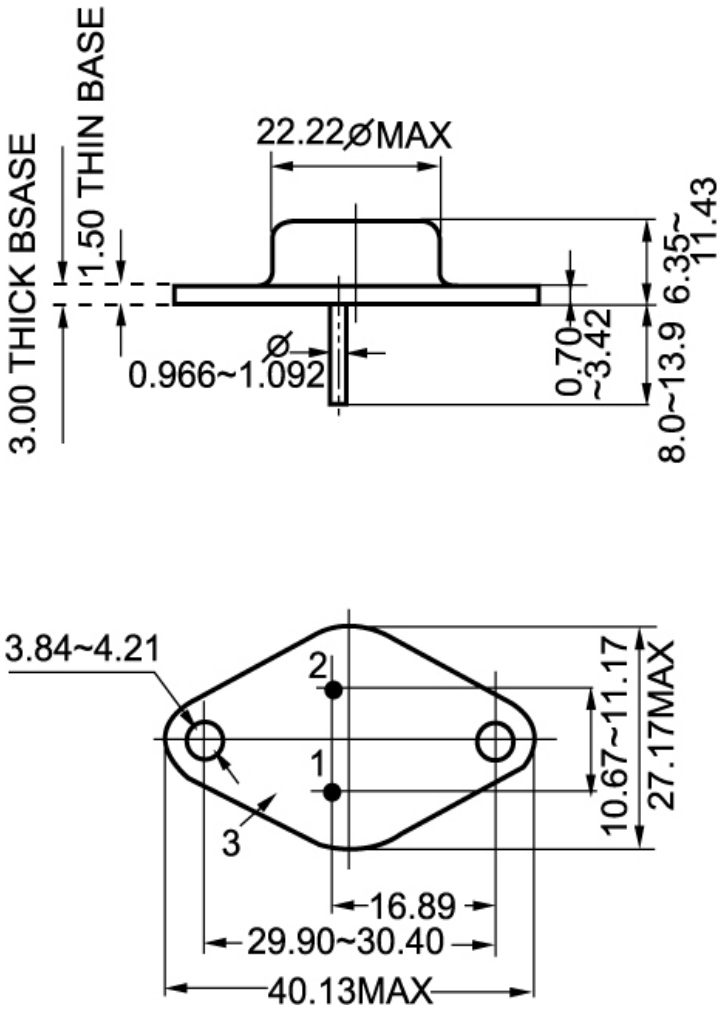

Fig.2 outline dimensions (unindicated tolerance:±0.1mm)